

CLAIM AMENDMENTS

1. (Currently Amended) A method for manufacturing a semiconductor device comprising ~~the steps of:~~
forming a film to be processed on a substrate;
forming a mask material on the film to be processed;
forming a resist pattern on the mask material;
patterning the mask material using the resist pattern as a mask;
~~shrinking a patterned~~ shrinking the mask material after patterning;
~~patterning the film to be processed using a shrunk~~ patterning the film to be processed using the mask material, after shrinking,
as a mask; and
removing the ~~shrunk~~ mask material.

2. (Currently Amended) The method for manufacturing a semiconductor device according to claim 1, wherein the mask material is a metal film ~~is formed as the mask material.~~

3. (Currently Amended) The method for manufacturing a semiconductor device according to claim 2, ~~wherein~~ including
forming a ruthenium film is formed as the mask material, and
~~the shrunk mask material is removed~~ removing together with the mask material and
the resist pattern using in an oxygen-containing plasma.

4. (Currently Amended) A method for manufacturing a semiconductor device comprising ~~the steps of:~~
forming a film to be processed on a substrate;
forming a ruthenium film as a mask material on the film to be processed;
forming a resist pattern on the mask material;
patterning the mask material using the resist pattern as a mask;
~~patterning the film to be processed using a patterned~~ patterning the film to be processed using the mask material, after
patterning, as a mask; and
removing the ~~patterned~~ mask material.

5. (Currently Amended) The method for manufacturing a semiconductor device according to claim 4, ~~wherein~~ including removing the patterned mask material is removed
together with the resist pattern using in an oxygen-containing plasma.

6. (Currently Amended) The method for manufacturing a semiconductor device according to claim 5, ~~wherein~~ including removing the patterned mask material is removed in the state that with a metal material ~~is~~ exposed on the substrate.